

# Publikačný seminár

## B. Zaťko:

Study of the contrast resolution of Timepix detector with a semi-insulating GaAs sensor,  
*J. Instrument.*

## J. Osvald:

Schottky barrier height inhomogeneity in 4H-SiC surface barrier detectors  
*Appl. Surf. Sci.*

## O. Pohorelec:

Investigation of interfaces and threshold voltage instabilities in normally-off MOS-gated  
InGaN/AlGaN/GaN HEMTs  
*Appl. Surf. Sci.*

## P. Šichman:

Semi-insulating GaN for vertical structures: role of substrate selection and growth pressure  
*Mater. Sci Semicond. Process.*

**Čas: 20. 08. 2020 o 10:00 hod. Miesto: veľká zasadačka EIÚ SAV, miestnosť 101**